

C1
said counterdoped channel region having a first doped region of opposite conductivity type and a second doped region underlying the first doped region of said opposite conductivity type, said second doped region having a lower effective dopant concentration than said first doped region, said second doped region being the primary conduction channel between said source and said drain[; a source adjacent to the channel; and a drain adjacent to the channel]

Amend claim 7 as follows:

C2 p. 1057
7. (Twice Amended) A semiconductor device comprising:

a substrate of a first conductivity type containing a plurality of field effect transistors, at least one of the field effect transistors having a counterdoped channel of opposite conductivity type, a source of said first conductivity type adjacent to the channel, a drain of said first conductivity type adjacent to the channel and spaced from said source, all disposed in said substrate, and a gate overlying the channel;

said counterdoped channel comprising a first doped region of said opposite conductivity type and a second doped region underlying the first doped region of said opposite conductivity type, said second doped region having a lower effective dopant concentration than said first doped region, said second doped region being the primary conduction channel between said source and said drain.